



DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(on)} max	I _D max T _A = +25°C
30V	$16m\Omega$ @ $V_{GS} = 10V$	9.8A
	$23m\Omega$ @ $V_{GS} = 4.5V$	8.7A

Description

This MOSFET is designed to minimize the on-state resistance $(R_{DS(on)})$ and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Backlighting
- Power Management Functions
- DC-DC Converters

Features

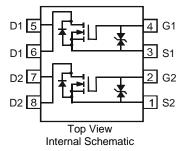
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected Up To 2kV
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Mechanical Data

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Weight: 0.072 grams (Approximate)







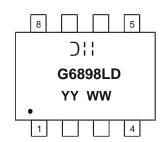
Ordering Information (Notes 4 & 5)

Part Number	Qualification	Case	Packaging
DMG6898LSD-13	Commercial	SO-8	2,500 / Tape & Reel
DMG6898LSDQ-13	Automotive	SO-8	2,500 / Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product_compliance_definitions/.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



Oll = Manufacturer's Marking
G6898LD = Product Type Marking Code
YYWW = Date Code Marking
YY or YY = Year (ex: 14 = 2014)
WW = Week (01 - 53)

DMG6898LSD 1 of 6
Document number: DS31947 Rev. 6 - 2
Downloaded From Oneyac.com



Maximum Ratings @TA = +25°C unless otherwise specified

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	20	V
Gate-Source Voltage			V_{GSS}	±12	V
Continuous Drain Current (Note 6)	Steady State	$T_A = +25^{\circ}C$ $T_A = +85^{\circ}C$	I _D	9.5 7.1	А
Pulsed Drain Current (Note 7)			I _{DM}	30	Α

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 6)	P_{D}	1.28	W
Thermal Resistance, Junction to Ambient @T _A = +25°C (Note 6)	$R_{\theta JA}$	99.3	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics @T_A = +25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)					•		
Drain-Source Breakdown Voltage	BV _{DSS}	20	-	-	V	$V_{GS} = 0V$, $I_{D} = 250\mu A$	
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	1	-	1.0	μΑ	$V_{DS} = 20V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	-	-	±10	μΑ	$V_{GS} = \pm 12V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	V _{GS(th)}	0.5	1.0	1.5	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance	0		11	16 23	mΩ	$V_{GS} = 4.5V, I_D = 9.4A$	
Static Drain-Source Off-Resistance	R _{DS (ON)}	-	17			$V_{GS} = 2.5V, I_D = 8.3A$	
Forward Transfer Admittance	Y _{fs}	-	17	-	S	$V_{DS} = 5V, I_{D} = 9.4A$	
Diode Forward Voltage	V_{SD}	-	0.7	1.2	V	$V_{GS} = 0V, I_{S} = 1.3A$	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	C _{iss}	-	1149	-	pF		
Output Capacitance	Coss	-	157	-	pF	$V_{DS} = 10V, V_{GS} = 0V,$	
Reverse Transfer Capacitance	Crss	-	142	-	pF	f = 1.0MHz	
Gate Resistance	Rg	-	1.51	-	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Qg	-	11.6	-	nC	V _{GS} = 4.5V, V _{DS} = 10V, I _D = 9.4A	
Total Gate Charge (V _{GS} = 10V)	Qg	-	26	-	nC		
Gate-Source Charge	Q _{qs}	-	2.7	-	nC		
Gate-Drain Charge	Q _{qd}	-	3.4	-	nC		
Turn-On Delay Time	t _{D(on)}	-	11.67	-	ns	$V_{DD} = 10V, V_{GS} = 4.5V,$ $R_{GEN} = 6\Omega, I_D = 1A$	
Turn-On Rise Time	t _r	-	12.49	-	ns		
Turn-Off Delay Time	t _{D(off)}	-	35.89	-	ns		
Turn-Off Fall Time	t _f	-	12.33	-	ns		

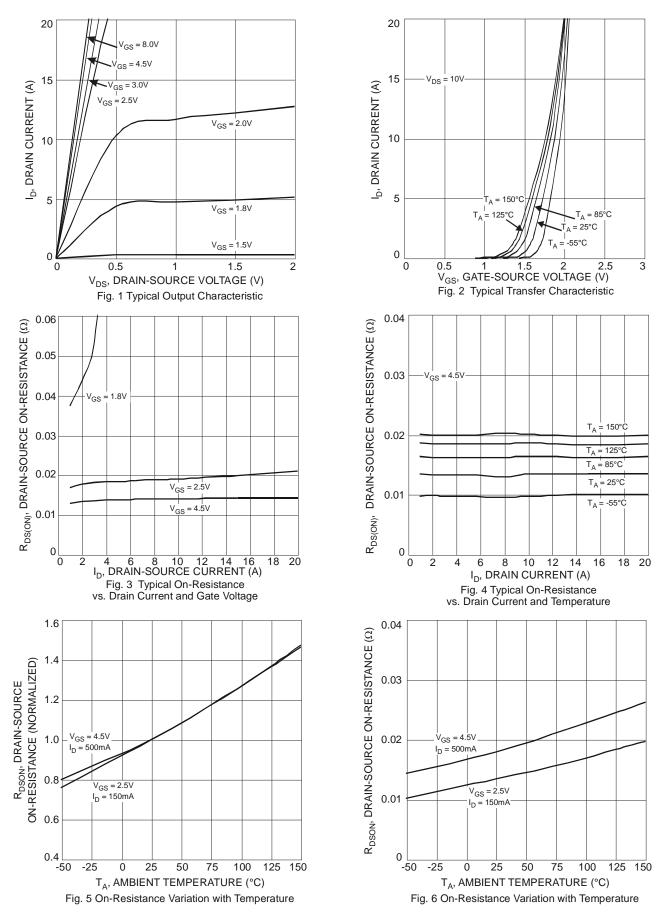
Notes:

- Device mounted on FR-4 PCB, with minimum recommended pad layout.
 Repetitive rating, pulse width limited by junction temperature.
 Short duration pulse test used to minimize self-heating effect.

- 9. Guaranteed by design. Not subject to production testing.

DMG6898LSD 2 of 6 Document number: DS31947 Rev. 6 - 2







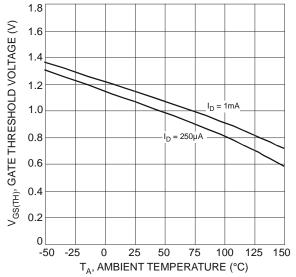
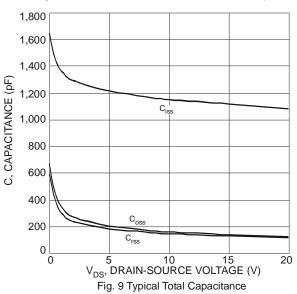


Fig. 7 Gate Threshold Variation vs. Ambient Temperature



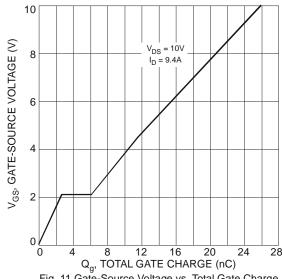
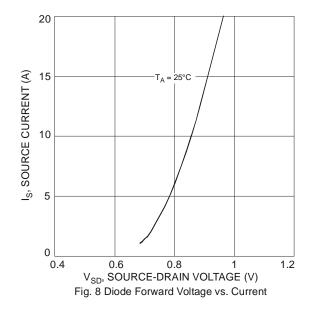
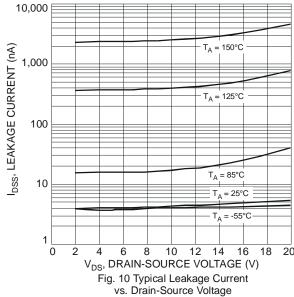
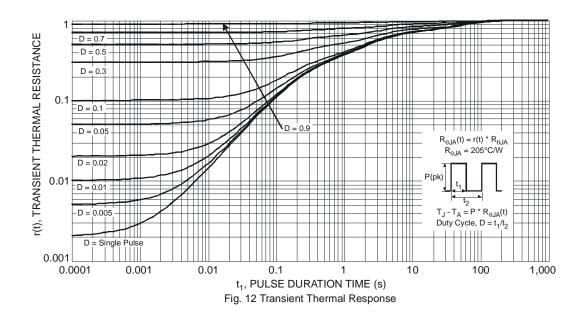


Fig. 11 Gate-Source Voltage vs. Total Gate Charge



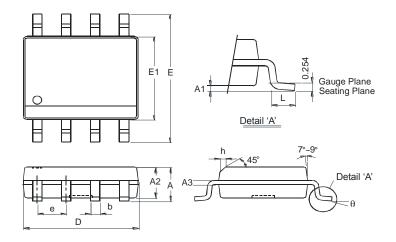






Package Outline Dimensions

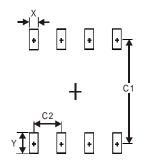
Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



SO-8				
Dim	Min	Max		
Α	-	1.75		
A 1	0.10	0.20		
A2	1.30	1.50		
A3	0.15	0.25		
b	0.3	0.5		
D	4.85	4.95		
Е	5.90	6.10		
E1	3.85	3.95		
е	1.27 Typ			
h	-	0.35		
L	0.62	0.82		
θ	0°	8°		
All Dimensions in mm				

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
X	0.60
Y	1.55
C1	5.4
C2	1.27



IMPORTANT NOTICE

DIODES INCORPORATED MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. Diodes Incorporated does not assume any liability arising out of the application or use of this document or any product described herein; neither does Diodes Incorporated convey any license under its patent or trademark rights, nor the rights of others. Any Customer or user of this document or products described herein in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on Diodes Incorporated website, harmless against all damages.

Diodes Incorporated does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel. Should Customers purchase or use Diodes Incorporated products for any unintended or unauthorized application, Customers shall indemnify and hold Diodes Incorporated and its representatives harmless against all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application.

Products described herein may be covered by one or more United States, international or foreign patents pending. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks.

This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes Incorporated.

LIFE SUPPORT

Diodes Incorporated products are specifically not authorized for use as critical components in life support devices or systems without the express written approval of the Chief Executive Officer of Diodes Incorporated. As used herein:

- A. Life support devices or systems are devices or systems which:
 - 1. are intended to implant into the body, or
 - 2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.
- B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.

Copyright © 2014, Diodes Incorporated

www.diodes.com

6 of 6 DMG6898LSD Document number: DS31947 Rev. 6 - 2

单击下面可查看定价,库存,交付和生命周期等信息

>>Diodes Incorporated(达尔科技)